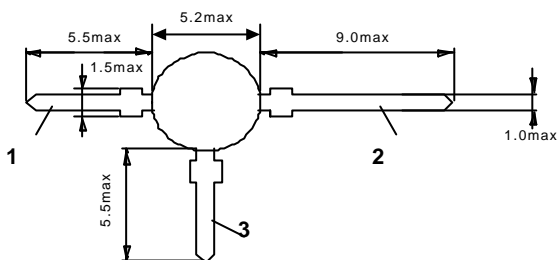


BFR96

N-P-N bipolar silicon RF transistor
in plastic package SOT-37

**Pinouts:**

1- Base, 2- Collector, 3-Emitter

Ratings

Symbol	Parameter, unit	Limits
V_{CBO}	Collector- base voltage, V	20
V_{CEO}	Collector- emitter voltage, V	15
V_{EBO}	Emitter- base voltage, V	3
I_C	Collector current, mA	75
P_{tot}	Power dissipation, mW	700

Characteristics ($T_A = 25^\circ\text{C}$)

Symbol	Parameter, unit, test conditions	Limits	
		min	max
f_T	Transition frequency, GHz, $I_E=50\text{mA}$, $V_{CB}=10\text{V}$	3.2	
h_{FE}	DC current gain, $I_E=50\text{mA}$, $V_{CB}=10\text{V}$	50	
I_{CBO}	Collector cut-off current, nA, $I_E=0\text{mA}$, $V_{CB}=10\text{V}$		100
G_{PS}	Power gain, dB, $I_E=50\text{mA}$, $V_{CE}=10\text{V}$, $f=500\text{MHz}$	13.0	
F	Noise figure, dB $I_E=50\text{mA}$, $V_{CE}=10\text{V}$, $f=500\text{MHz}$		4.0
C_C	Collector capacitance, pF, $V_{CB}=10\text{V}$, $f=1\text{MHz}$		2.0